

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

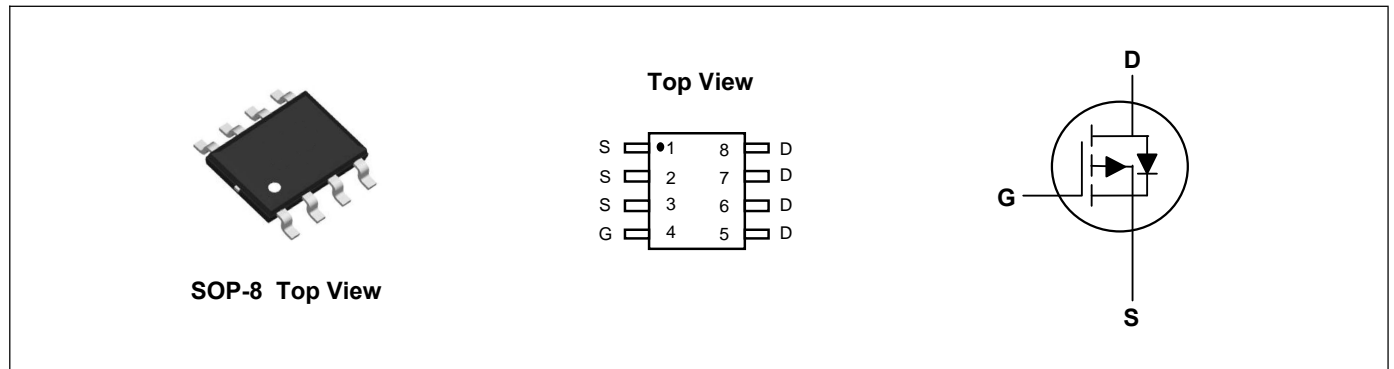
Product Summary



V_{DS}	-30	V
I_D	-9.1	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	20	m Ω
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	35	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@T_A=25^{\circ}C$	-9.1	A
Continuous Drain Current	$I_D@T_A=70^{\circ}C$	-7.2	A
Pulsed Drain Current ²	I_{DM}	-50	A
Total Power Dissipation	P_D	3.1	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	40	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	---	---	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-9.1A	---	16	20	mΩ
		V _{GS} =-4.5V, I _D =-6.9A	---	21	35	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =-250uA	-1	-1.5	-3	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =-15V, I _D =-9.1A	10	---	---	S
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-10V, I _D =-9.1A	---	30	---	nC
Gate-Source Charge	Q _{gs}		---	5.5	---	
Gate-Drain Charge	Q _{gd}		---	8	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω	---	10	---	ns
Rise Time	T _r		---	15	---	
Turn-Off Delay Time	T _{d(off)}		---	110	---	
Fall Time	T _f		---	70	---	
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1600	---	pF
Output Capacitance	C _{oss}		---	350	---	
Reverse Transfer Capacitance	C _{rss}		---	300	---	

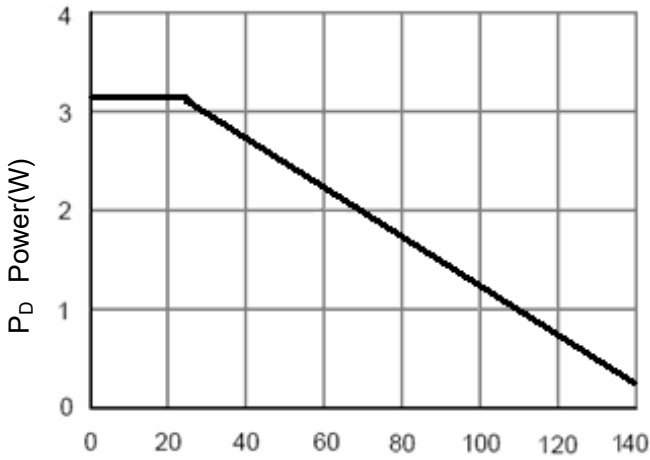
Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ¹	V _{SD}	V _{GS} =0V, I _S =-9.1A, T _J =25°C	---	---	-1.2	V

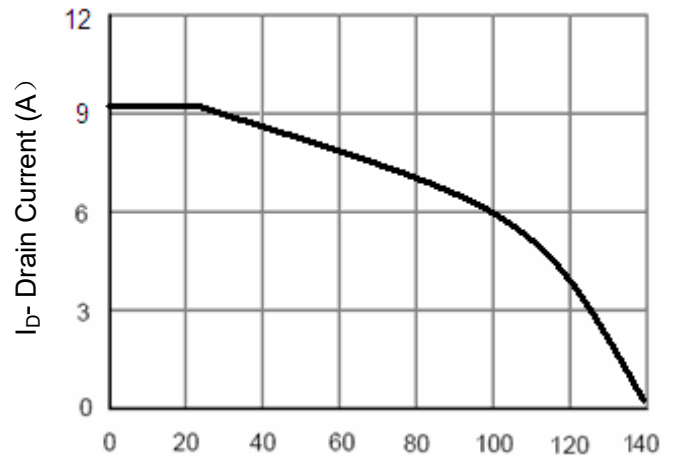
Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

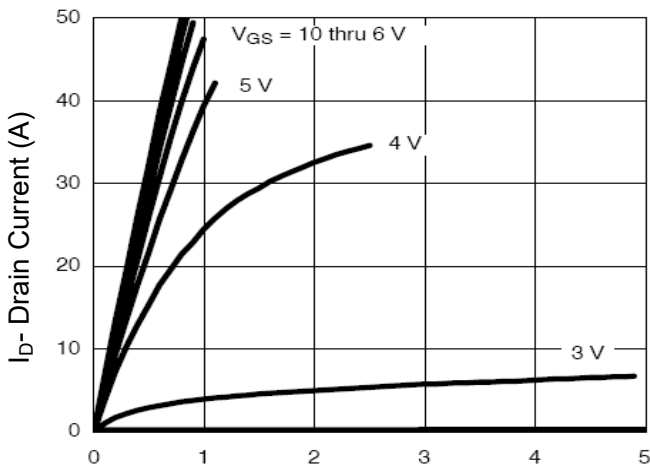
Typical Characteristics



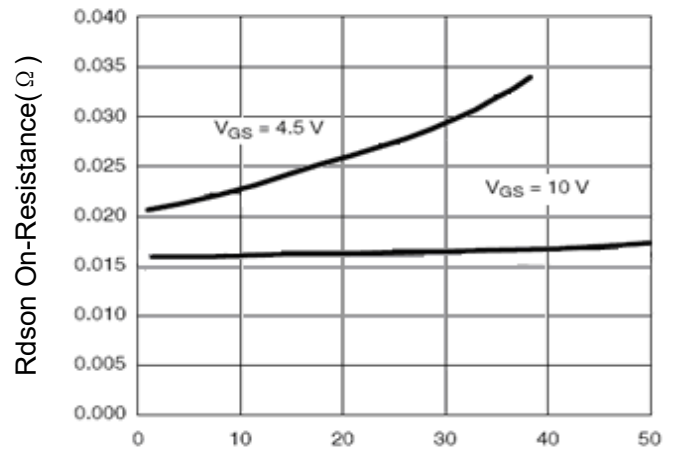
T_J-Junction Temperature(°C)
Figure 1 Power Dissipation



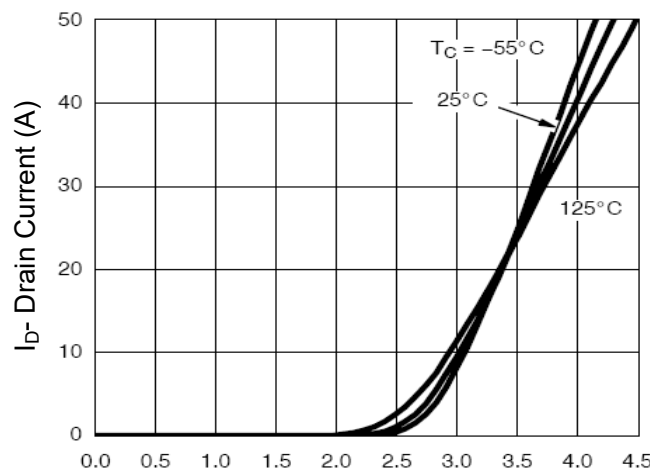
T_J-Junction Temperature(°C)
Figure 2 Drain Current



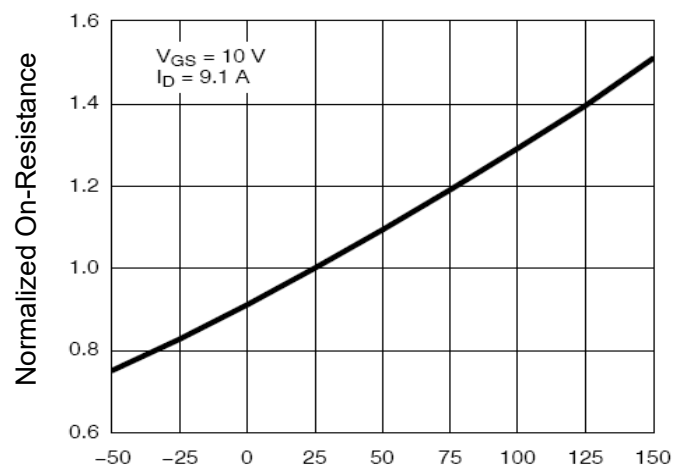
V_{ds} Drain-Source Voltage (V)
Figure 3 Output Characteristics



Id- Drain Current (A)
Figure 4 Drain-Source On-Resistance



V_{GS} Gate-Source Voltage (V)
Figure 5 Transfer Characteristics



T_J-Junction Temperature(°C)
Figure 6 Drain-Source On-Resistance

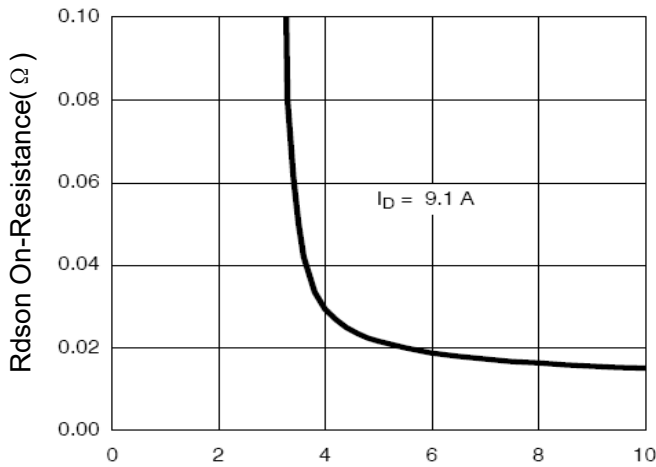


Figure 7 Rdson vs Vgs

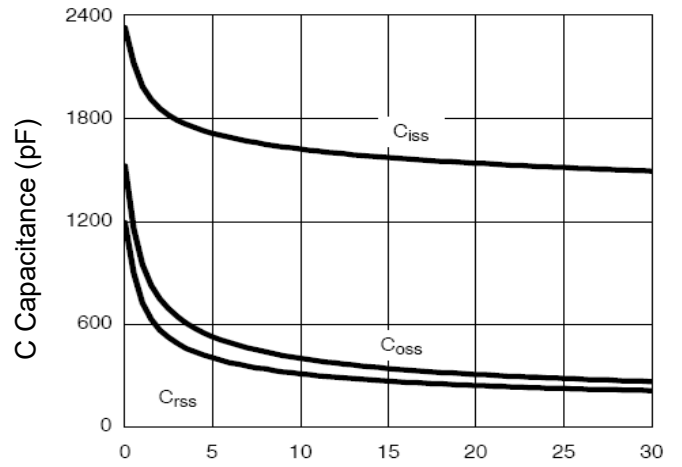


Figure 8 Capacitance vs Vds

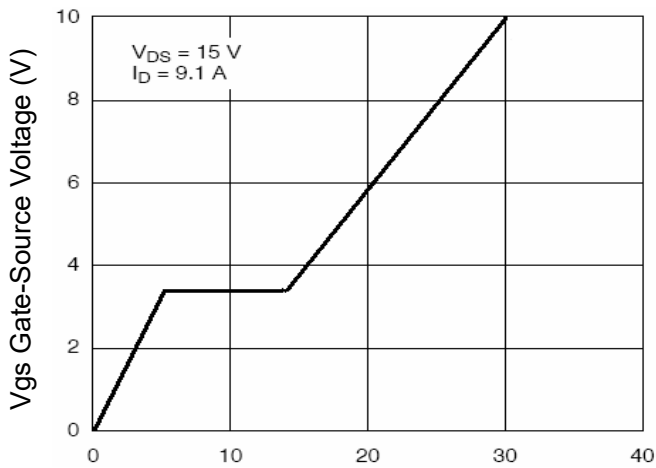


Figure 9 Gate Charge

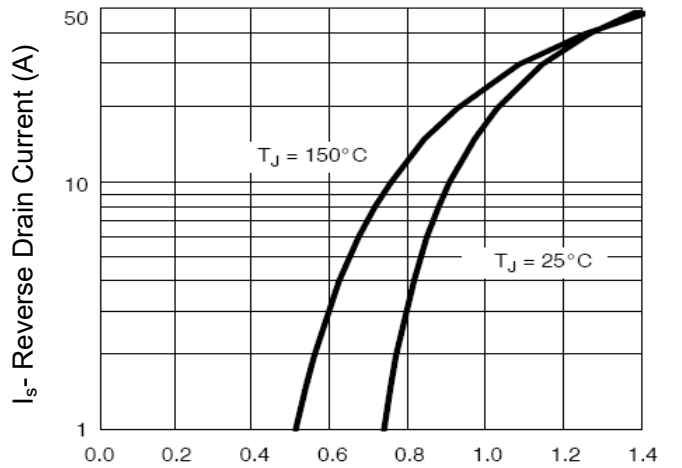


Figure 10 Source- Drain Diode Forward

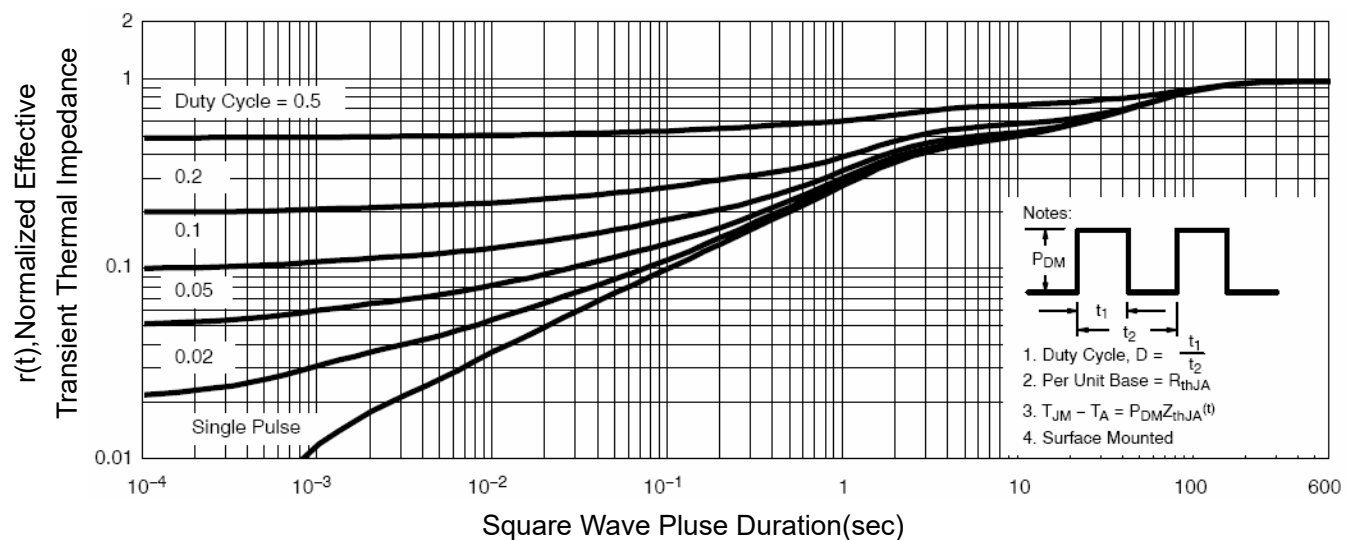


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	1.35	1.55	1.75	A₁	0.10	0.18	0.25
A₂	1.25	1.45	1.65	A₃	--	0.25	--
b_p	0.36	0.42	0.51	c	0.19	0.22	0.25
D	4.70	4.92	5.10	E	3.80	3.90	4.00
e	--	1.27	--	H_E	5.80	6.00	6.20
L	--	1.05	--	L_p	0.40	0.68	1.00
Q	0.60	0.65	0.73	v	--	0.25	--
w	--	0.25	--	y	--	0.10	--
Z	0.30	0.50	0.70	θ	0°		8°